

60V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _(BR) DSS	R _{DS(on)} Max	I _D Max T _A = 25°C (Note 5)	
-60V	125m Ω @ V _{GS} = -10V	-3.0 A	
-00 V	190mΩ @ $V_{GS} = -4.5V$	-2.4 A	

Description and Applications

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- · Power management functions
- Disconnect switches
- Motor control

Features and Benefits

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low input capacitance
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

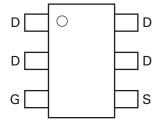
Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper lead frame.
 Solderable per MIL-STD-202, Method 208
- Weight: 0.018 grams (approximate)

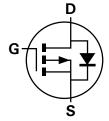




Top View



Pin Out - Top View



Equivalent Circuit

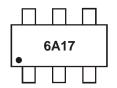
Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP6A17E6TA	6A17	7	8	3,000

Notes:

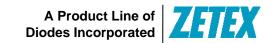
- 1. No purposefully added lead
- 2. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



6A17 = Product Type Marking Code





Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source voltage		V_{DSS}	-60	V	
Gate-Source voltage			V_{GS}	±20	V
		(Note 5)		-3.0	
Continuous Drain current	$V_{GS} = 10V$	$T_A = 70$ °C (Note 5)	I_{D}	-2.4	Α
		(Note 4)		-2.3	
Pulsed Drain current	$V_{GS} = 10V$	(Note 6)	I _{DM}	-13.6	Α
Continuous Source current (Body diode) (Note 5)		I _S	-2.5	Α	
Pulsed Source current (Body diode) (Note 6)		I _{SM}	-13.6	Α	

Thermal Characteristics @TA = 25°C unless otherwise specified

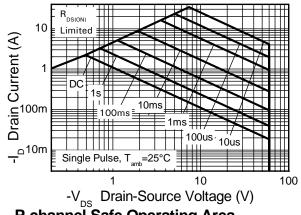
Characteristic		Symbol	Value	Unit	
Power dissipation	(Note 4)		1.1 8.8	W	
Linear derating factor	(Note 5)	P _D	1.92 15.4	mW/°C	
Thermal Resistance, Junction to Ambient	(Note 4)	R _{eJA}	113	°C/W	
Thermal Resistance, sunction to Ambient	(Note 5)	N _θ JA	65		
Operating and storage temperature range		T _J , T _{STG}	-55 to 150	°C	

Notes:

- 4. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 5. Same as note (4), except the device is measured at $t \le 5$ sec.
- 6. Same as note (4), except the device is pulsed with D = 0.02 and pulse width 300 μs. The pulse current is limited by the maximum junction temperature.



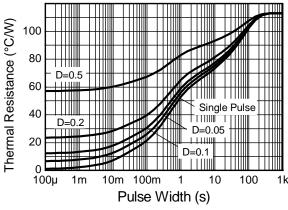
Thermal Characteristics

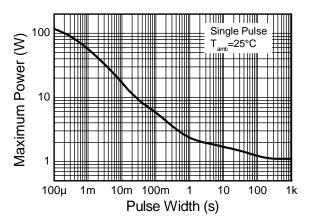


1.2 Max Power Dissipation (W) 1.0 0.8 0.6 0.2 0.0 25 75 100 Temperature (°C)

P-channel Safe Operating Area

Derating Curve





Transient Thermal Impedance

Pulse Power Dissipation





Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-60		_	V	$I_D = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1.0	μΑ	$V_{DS} = -60V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	_	-3.0	V	$I_D = -250 \mu A$, $V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 7)	В		0.100	0.125	Ω	$V_{GS} = -10V, I_D = -2.3A$	
Static Dialif-Source Off-Resistance (Note 7)	R _{DS} (ON)	_	0.130	0.190	12	$V_{GS} = -4.5V$, $I_{D} = -1.9A$	
Forward Transconductance (Notes 7 & 8)	9 _{fs}	_	4.7	_	S	$V_{DS} = -15V, I_{D} = -2.3A$	
Diode Forward Voltage (Note 7)	V_{SD}	_	-0.85	-0.95	V	$I_S = -2A$, $V_{GS} = 0V$	
Reverse recovery time (Note 8)	t _{rr}		25.1	_	ns	-I _F = -1.7A, di/dt = 100A/μs	
Reverse recovery charge (Note 8)	Q_{rr}	_	27.2	_	nC		
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	637	_	pF		
Output Capacitance	Coss	_	70	_	pF	$V_{DS} = -30V, V_{GS} = 0V$ - f = 1MHz	
Reverse Transfer Capacitance	Crss	_	53	_	pF	1 = 1101112	
Total Gate Charge (Note 9)	Q_g	_	9.8	_	nC	V _{GS} = -5.0V	
Total Gate Charge (Note 9)	Qq	_	17.7	_	nC	V _{DS} = -30V	
Gate-Source Charge (Note 9)	Q _{gs}	_	1.6	_	nC	$V_{GS} = -10V$ $I_{D} = -2.3A$	
Gate-Drain Charge (Note 9)	Q_{gd}	_	4.4	_	nC		
Turn-On Delay Time (Note 9)	t _{D(on)}	_	2.6	_	ns		
Turn-On Rise Time (Note 9)	t _r	_	3.4	_	ns	$V_{DD} = -30V, V_{GS} = -10V$ $I_{D} = -1A, R_{G} \approx 6.0\Omega$	
Turn-Off Delay Time (Note 9)	t _{D(off)}	_	26.2	_	ns		
Turn-Off Fall Time (Note 9)	t _f	_	11.3	_	ns		

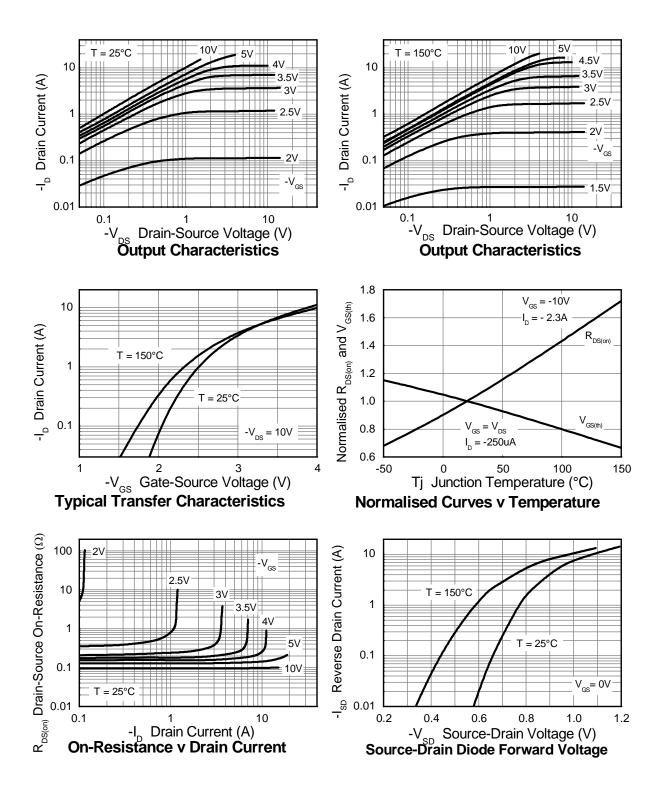
Notes:

- Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%
 For design aid only, not subject to production testing.
 Switching characteristics are independent of operating junction temperatures.



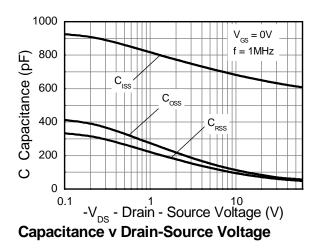


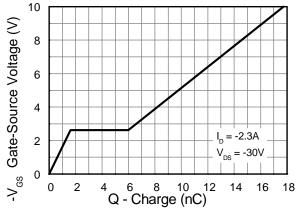
Typical Characteristics





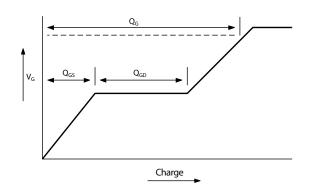
Typical Characteristics - continued





Gate-Source Voltage v Gate Charge

Test Circuits

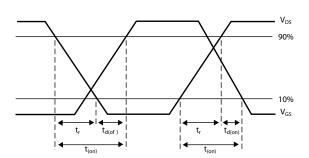


Current regulator

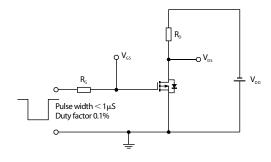
12V 0.2µF 50k D.U.T

Vos

Basic gate charge waveform



Gate charge test circuit



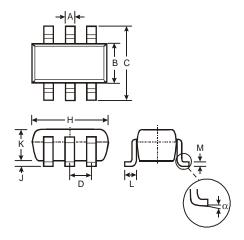
Switching time waveforms

Switching time test circuit



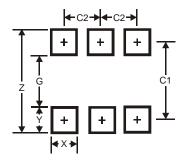


Package Outline Dimensions



	SOT-26					
Dim	Min	Max	Тур			
Α	0.35	0.50	0.38			
В	1.50	1.70	1.60			
С	2.70	3.00	2.80			
D			0.95			
Н	2.90	3.10	3.00			
J	0.013	0.10	0.05			
K	1.00 1.30 1.1		1.10			
٦	0.35	0.55	0.40			
M	0.10	0.20	0.15			
α	α 0° 8° —					
All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Υ	0.80
C1	2.40
C2	0.95





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